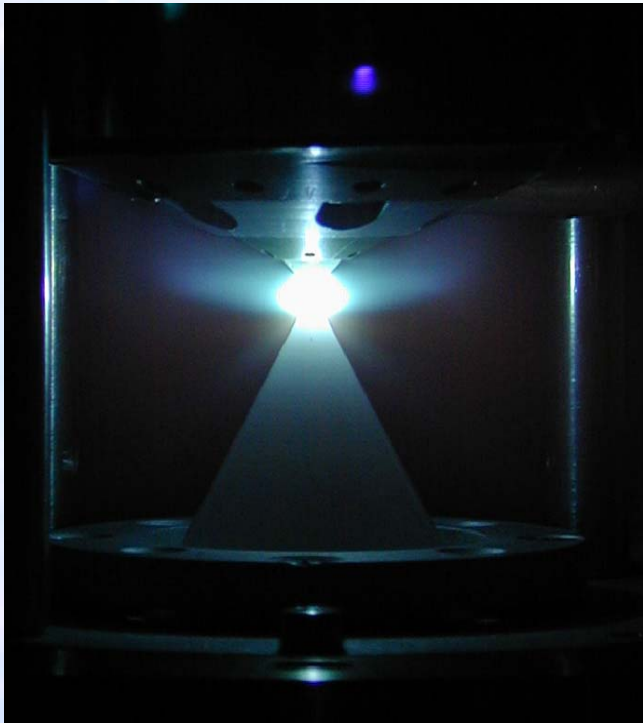


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Modular Laser Produced Plasma Source For EUV Lithography



The Exulite Project Team:

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*Presented by B. Fay (Consultant, Euris Consulting)



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OUTLINE

A large, stylized blue arrow graphic pointing to the left, with a jagged, cloud-like edge, positioned below the 'OUTLINE' header.

- ◆ Introduction
- ◆ Goal of the EXULITE project
- ◆ Previous Work: PREUVE LPP source
- ◆ ELSAC LPP source
- ◆ Source Roadmap
- ◆ Summary



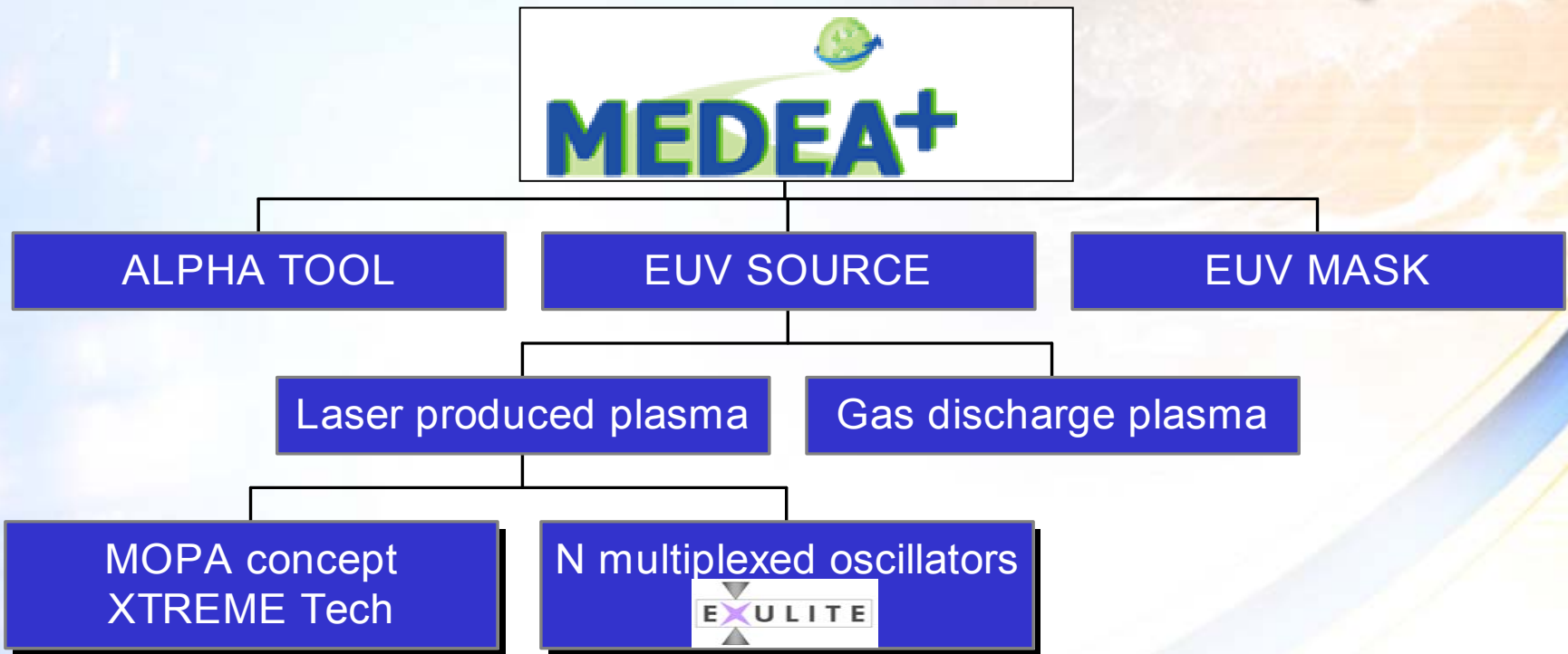
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WITHIN MEDEA+*



* MEDEA+ label obtained in May 2001

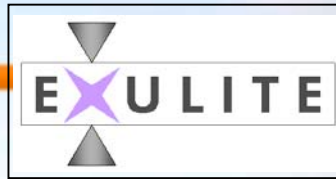


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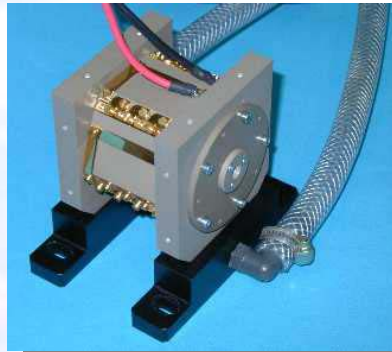
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EXULITE Project Partners

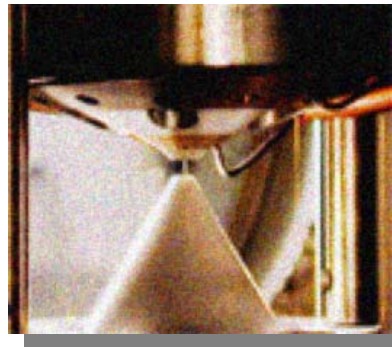


Coordinator : Alcatel

EXULITE Organization



**Lower cost laser
High reliability**



**Process optimization
Characterization
Optical interface**



**Vacuum, Xe recycling
Monitoring
System integration,**

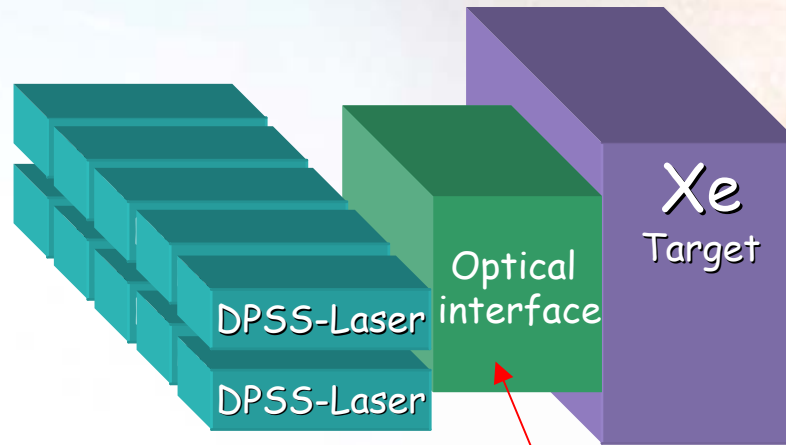


- ◆ **Develop a High Performance, Modular LPP source for EUV Lithography**
 - ◆ EUV output power: 50W
 - ◆ Laser power: $\geq 5\text{kW}$ (N multiplexed oscillators)
 - ◆ Source rep rate : 10kHz
 - ◆ Target: Recycled Xe jet
 - ◆ Conversion efficiency: $\geq 1\%$
 - ◆ Availability: 2005

- ◆ **Patent on Xe target (spray of droplets) and recycling**
 - ◆ Low debris (Xe)
 - ◆ Xenon recycling (reduction of C.o.O.)
 - ◆ Contamination control in order to increase the lifetime of optics
- ◆ **Patent on laser multiplexing**
 - ◆ Scalable power
 - ◆ Modular approach:
 - Optimization of development and manufacturing costs
 - Reliability
 - Easier maintenance
 - ◆ High pulse to pulse energy stability
 - ◆ Good beam quality for better focusability

Patented* Design of Modular LPP Source

N identical DPSS
(Diode pumped solid state)
laser units



Multiplexer

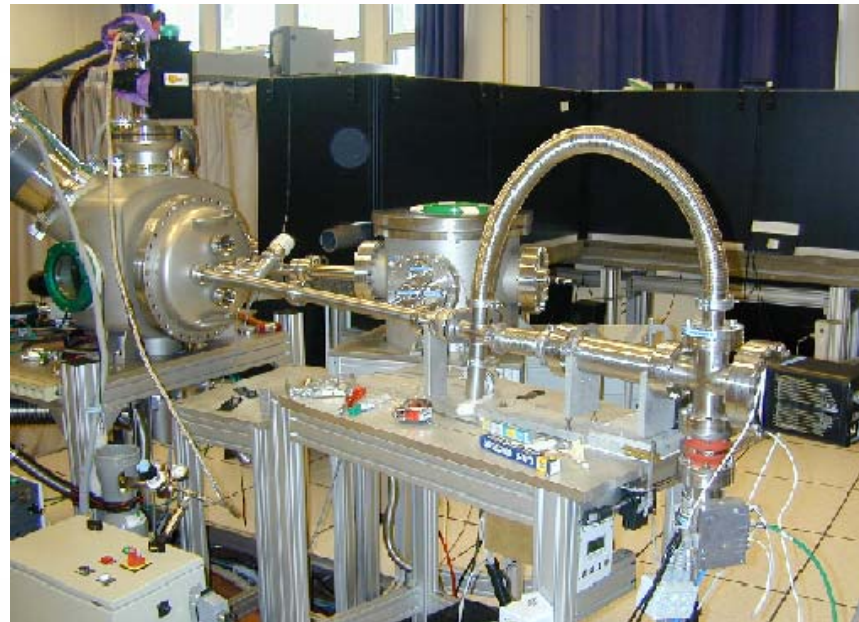


Advantages : efficiency, simplicity, compactness,
reliability, reduced cost.

*WO 02/27 872

Previous Work: PREUVE LPP Source

- ◆ CEA/SPAM has developed a Xe LPP source for the EUV Test Bench (BEL) within the PREUVE program
- ◆ The BEL tool will be used within the “Excite project of MEDEA+”
- ◆ Thales has demonstrated in the second phase of the PREUVE program a 300W, 10kHz DPSS oscillator module



Performances of the ELSA (PREUVE) Source

- ✓ Performances of the ELSA source :
 - 35 W Nd:YAG pump laser power
 - 250 mW (EUV power in $2\pi\text{sr}^*$)
 - CE = 0.71% (in $2\pi\text{sr}^*$)
 - 8.0 mW (useful EUV power in 0.2sr^*)
- ✓ Exposure time with BEL : less than 1 sec
assuming sensitivity of $100\text{mJ}/\text{cm}^2$
static exposure field of $(100\mu\text{m})^2$
and 2.5% EUV transmission of BEL

* 2.5% BW @ 13.5 nm

Today's performances of the modified ELSA source

- ✓ Modified ELSA prototype using a continuous cryogenic target
- ✓ Existing ELSA prototype and pumping system was not adapted to continuous operation, $CE^* = 0.20\%$ (2.5% bw, $2\pi sr$), optimization in process
- ✓ Present performances of modified ELSA is currently lower than expected because of strong EUV reabsorption (too high vessel pressure)
- ✓ Construction of the ELSAC prototype is underway to achieve optimized pumping

*This is an uncorrected value (with respect to the environmental pressure within the source chamber (CEx2 assuming 10^{-4} mbar))



ELSAC System Architecture and Development

- ✓ Detailed functional analysis of the whole ELSAC system is completed
- ✓ Recirculated Xenon to keep costs reasonable (<500 l/h)
- ✓ EUV Chamber contamination control
- ✓ Vibration control
- ✓ Thermal management
- ✓ Debris mitigation
- ✓ Full scalability of the source architecture
- ✓ High speed target for high repetition rate laser operation (far above 10kHz possible)
- ✓ Properties of the ELSAC platform (modularity, redundant design and architecture)

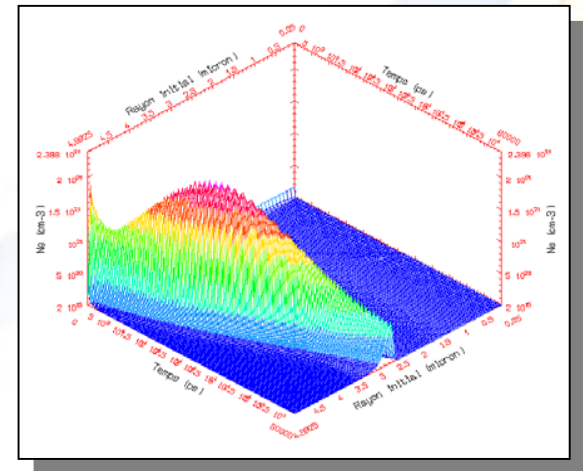
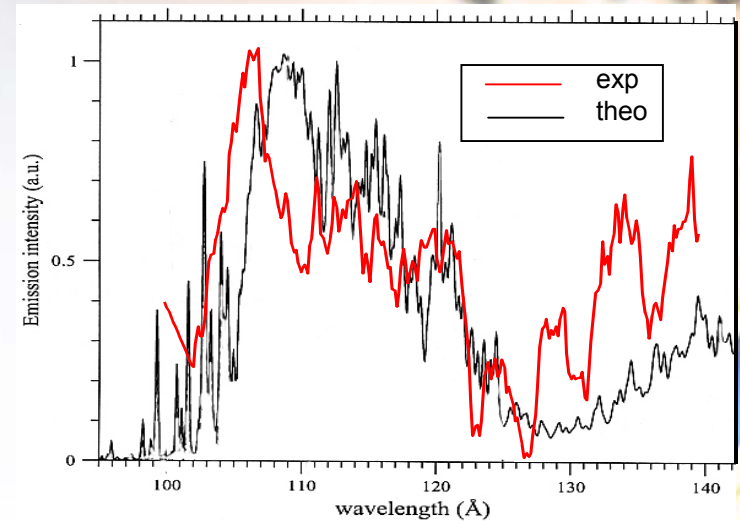
Numerical simulations at CEA to:

- enhance the plasma emissivity #
- improve the laser target coupling
- choose the best target material and composition

Approach: coupling a hydrodynamic code to collisional-radiative atomic physics code

CEA is a member of the Sematech EUV data workgroup

F. Gilleron, et al., J. Appl. Phys. (submitted 2002).



A complete set of Plasma and Source Diagnostics

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- ✓ Space (and *time) resolved EUV spectrograph
- ✓ Plasma diagnostics (e.g. Thomson scattering and 4ω interferometry)
- ✓ Multi pinhole frame camera (CEA/DAM)
- ✓ *Streak camera (CEA/DAM)
- ✓ Angular distribution measurement device





- ✓ Ionic debris of ELSA are quite energetic (15keV mean energy)
- ✓ Ionic erosion (and thermal load) requires for very specific nozzle materials (e.g. hardness and thermal conductivity)
- ✓ Within MEDEA+ T405, consulting at Innolite and Xtreme for debris characterization in 2002





Complementary Experiments

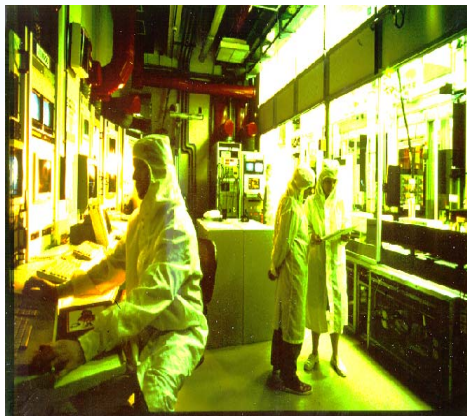
- ✓ Experiments on alternate target yields CE = 1.4 %
(3Q 2002)
- ✓ In situ thermal studies on jet using 4 - 8 kW cw laser in 100 μm spot
@ 1.064nm (1Q 2003)
- ✓ Test with 500W 10kHz laser module on continuous Xe target
(3Q 2003)
- ✓ Experiments on improved alternate targets
(4Q 2003)

Laser Development: Technical Background

- ✓ 10 years of experience developing complex optical systems (French AVLIS program)
- ✓ Patented design of high-power, diode-pumped solid-state-lasers



Patent on multiplexed laser
for producing a EUV source



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THALES Laser Involvement in the EXULITE Project

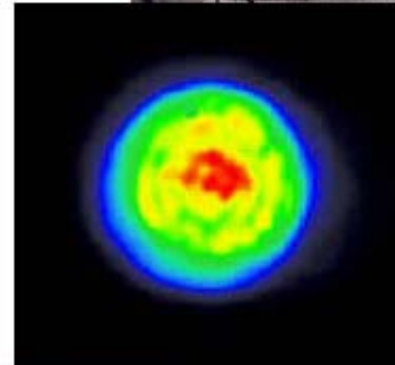
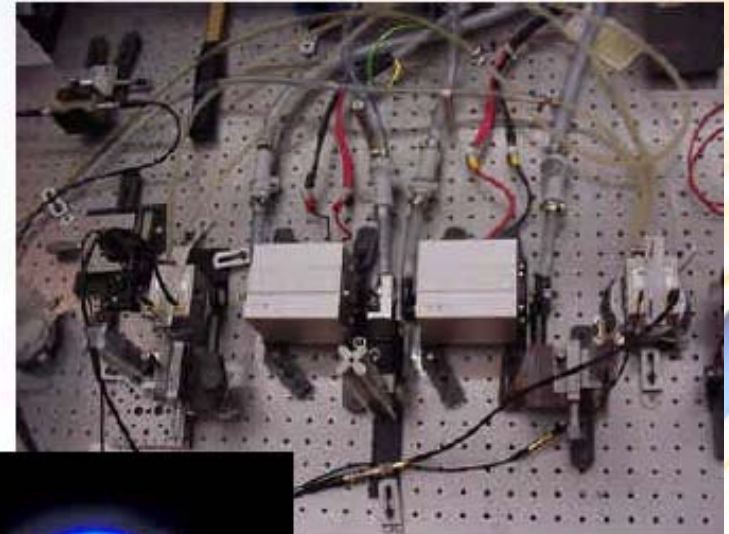
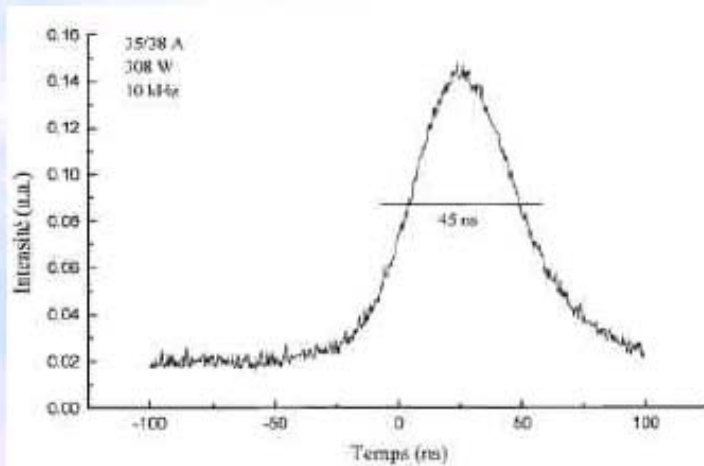


- ◆ Demonstration of 300W IR laser based on existing pumping chambers
- ◆ Development of 500W IR laser for EUV source based on more powerful pumping chambers: first prototype in August 2003
- ◆ Industrialization of ten 500W IR laser modules for the first quarter of 2004



300W IR Unit: Laser Demonstrator

λ	1064 nm
P_{AVG}	> 300 W
M^2	< 10
Repetition rate	10 kHz
Pulse duration	< 50 ns

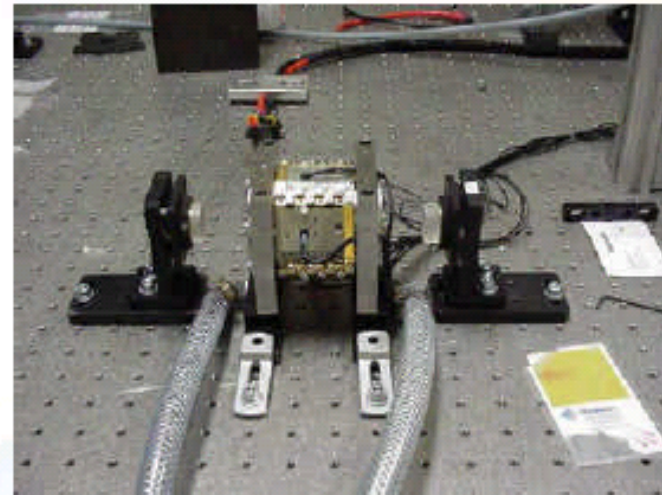
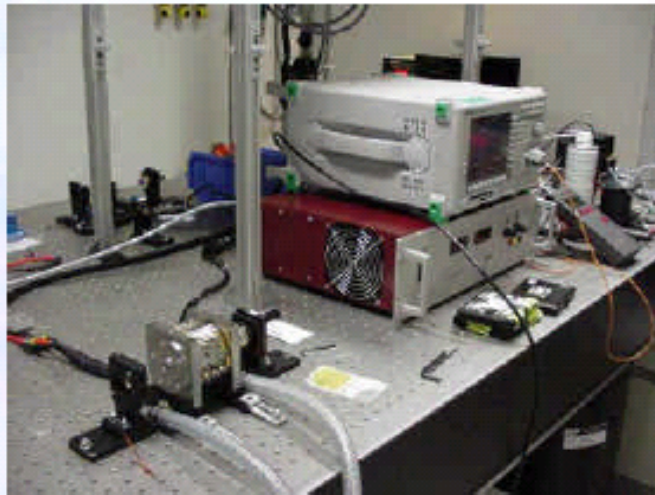


30 diodes heads under permanent operation at THALES

Laser laboratory

Up to now, 2000 hours of operation, inspection at 1200

Running till the end of the head



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Development of the 5 kW Laser System

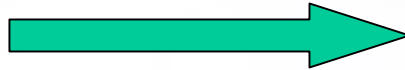
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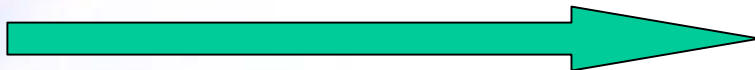


Development of the 500 W, 10 kHz, $M^2 = 10$ laser module



Coupling 2 modules to EUV source

Coupling 10 modules (5 kW) to EUV source



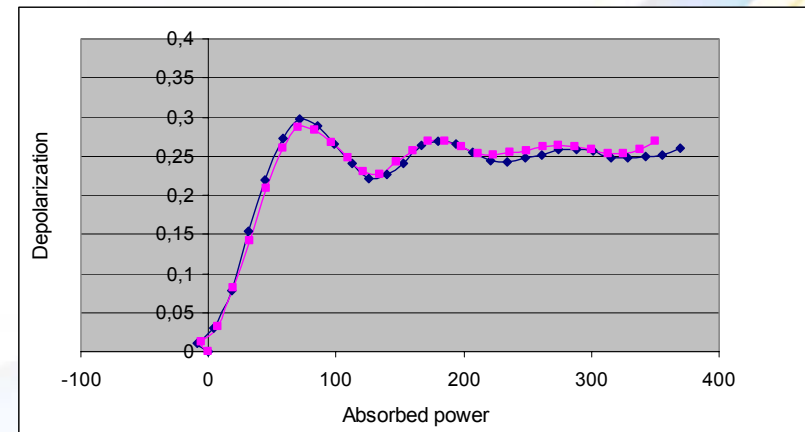
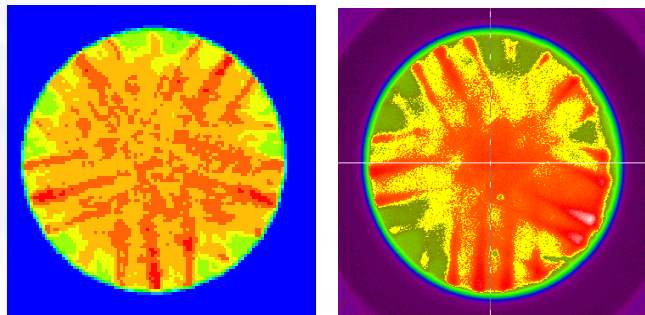
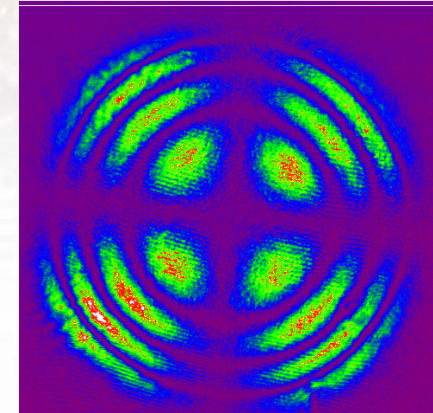
Design the multiplexing and focusing system



Challenges in Laser Technology

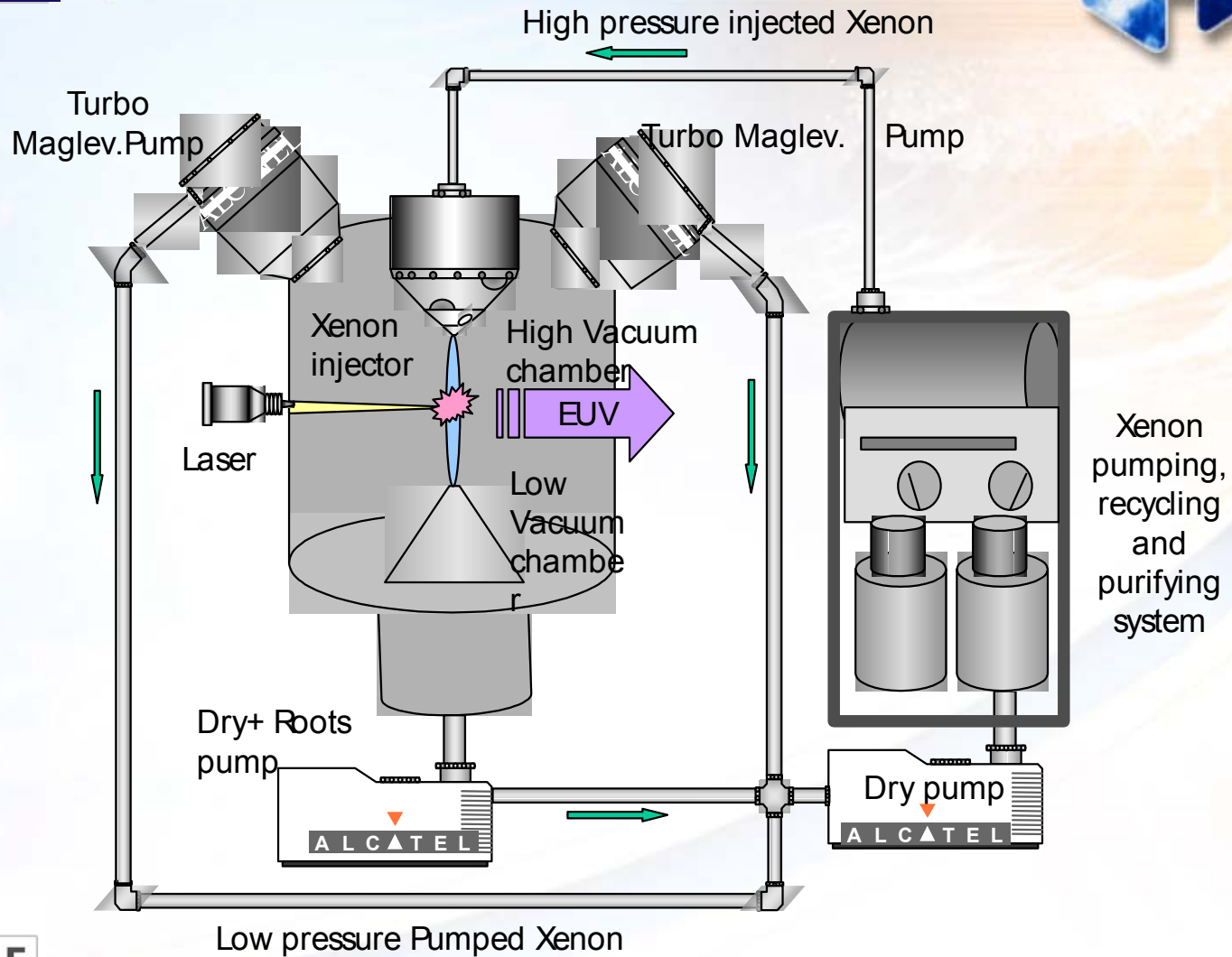
Filling the gap between 300 and 500 W :

- ✓ Modeling and minimizing thermal effects
- ✓ Optimizing the laser parameters (pulse length, beam quality, efficiency, ...)
- ✓ Further improving reliability, reducing costs





Xenon Pumping and Recycling System



Xenon Recycling and Purifying Principle

- ◆ Flexible tank to stock Xenon
- ◆ Specific filter units to purify xenon
- ◆ Physical transformation:
 - ◆ Cryogenic and heating means
 - ◆ Cycle is made continuous by using 3 identical tanks

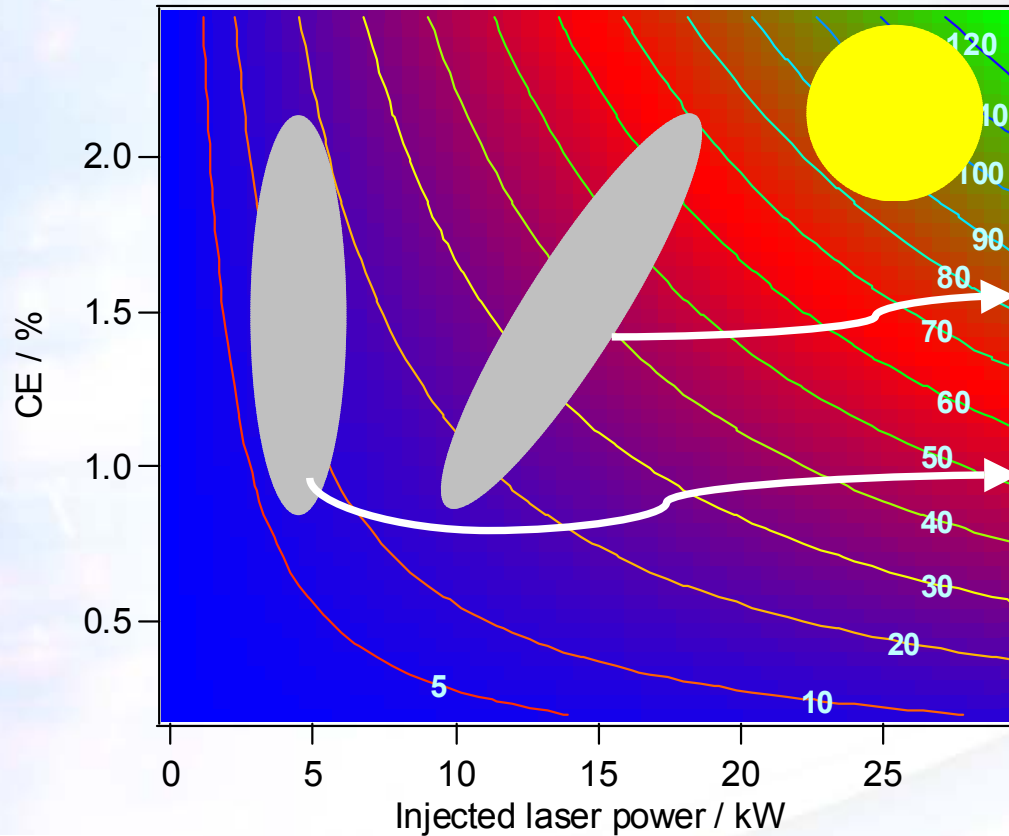


Xenon Recycling System Capacities

	Today	Tomorrow
Xenon Flow	0.4 slm ($3 \cdot 10^{-4}$ mol.s ⁻¹)	8 slm ($6 \cdot 10^{-3}$ mol.s ⁻¹ / adjustable < 1%)
Injected pressure	20 bar (+/- 10 %)	50 bar (adjustable from 1 to 50 bar)
Xenon purity	10 ppm H ₂ O 10 ppm O ₂ 10 ppm hydrocarbons	0.1 ppm H ₂ O, O ₂ and hydrocarbons 10 ppm N ₂ and rare gas 1 ppm other gases
Total xenon load	15 mol (~340L)	15 mol (~340L)

Development Roadmap of the ELSAC Laser-Produced Plasma Source

EUV in-band power in π sr @ intermediate focus #



Today's market request for industrial EUV steppers for 100wph

Source specs in 2006/07

Today's goal of EXULITE for 2004/05

#debris mitigation, spectral purity filter and gas transmission included



EXULITE Source Performance Roadmap

EXULITE Source Performance Roadmap

Metrics	Oct-00	Mar-01	Oct-01	Mar-02	Sep-02	Mar-03	Mar-04	Mar-05	Mar-06	Mar-07
Central wavelength (nm)	13	13.5	13.5	13.5	13.5	13.5	13.5	13.5	13.5	13.5
Demonstrated collectable EUV power in a 2% spectral bandwidth in the region between 13-14nm (W)	0.01	0.01	0.1	0.15	0.25	1	10	50	200	> 200
Available collection solid angle (sr)	1.5	1.5	1.5	2	2	π	π	π	2π	2π
Source emission area (mm ²)	0.2	0.2	0.2	0.03	0.03	0.01	0.01	0.01		
Etendue (mm ² -sr)					0.06	0.03	0.03	0.03		
Demonstrated maximum repetition rate (kHz)	0.01	0.01	0.05	0.05	0.05	5	6-12	6-12	> 12	> 12
Demonstrated steady state repetition rate (kHz)										
Dissipated total power in source region at steady state (kW)		0.035	0.035	0.035	0.035	0.2	1	5	10	> 10
Source facing condenser lifetime (# of pulses to 10% reflectance loss)										
Pulse-to-pulse spatial stability (um 3s)										
Pulse-to-pulse intensity stability (um 3s)										
Pulse-to-pulse angular stability (um 3s)										
Pulse-to-pulse pointing stability (um 3s)										
Key risk areas				nozzle	nozzle	nozzle	nozzle	CoO	CoO	CoO
Critical component lifetime (h)										

- ◆ **Modular LPP source with N multiplexed laser modules**
- ◆ **Partnership between CEA, Thales and Alcatel Vacuum, with Alcatel Vacuum as system integrator**
- ◆ **Goal: 50W EUV (in 2π sr) in 2005 for alpha tool**
 - ◆ Xe flow target for first source
 - ◆ Study of higher CE target materials underway
- ◆ **Roadmap to higher power**